

## VERSION SHOWING AMENDMENTS TO THE CLAIMS

This listing replaces all prior listings of the claims.

1 (Currently amended). An electronic organic component comprising at least two functional layers adjacent to one another, the first functional layer being produced from the same organic material as the second and adjacent functional layer but differing at least partly therefrom in its electrical physical properties ~~(such as, for example, the conductivity)~~.

2 (Currently amended). The electronic organic component as claimed in claim 1, in which one of the functional layers is semiconductive, the semiconductive functional Layer and ~~the conductive~~ at least one other functional layer~~(s)~~ differ only in their redox potential.

3 (Currently amended). A method for the production of an organic electronic component, in which two different functional layers are produced in a single process step by converting a part of a ~~the~~ functional layer into another functional layer by modification of the material by partial reaction.

4 (Currently amended). The method as claimed in claim 3, in which electrodes and/or conductor tracks and a semiconductive functional layer are produced with structuring in one process step and in one functional layer.

5 (Currently amended). The method as claimed in claim 3 ~~or 4~~ wherein one of the functional layers is a semiconductive layer, in which a conductive structure is ~~was~~ introduced in a controlled manner into the semiconductive functional layer by partial covering and treatment of the uncovered regions with a redox composition.

6 (Currently amended). The method as claimed in claim 3 ~~any of the above claims 3 to 5~~, in which one of the functional layers is a semiconductive layer and the semiconductive layer is covered by ~~means of~~ a photoresist.

7 (Currently amended). The method as claimed in claim 5 ~~any of the above claims 3 to 6~~, in which the redox composition is partially applied to the semiconductive functional layer by printing, ~~including inkjet printing~~.

8 (Currently amended). The method as claimed in claim 3 ~~any of the above claims 3 to 7~~, in which a time-stable partial oxidation of the semiconductive functional layer is carried out ~~by means of~~ an oxidizing agent.

Add the following claims:

9 (New). The method as claimed in claim 4, in which a conductive structure is introduced in a controlled manner into the semiconductive functional layer by partial covering and treatment of the uncovered regions with a redox composition.

10 (New). The method as claimed in claim 4 in which the semiconductive layer is covered by a photoresist.

11 (New). The method as claimed in claim 5 in which the semiconductive layer is covered by a photoresist.

12 (New). The method as claimed in claim 3 wherein one of the functional layers is a semiconductive functional layer in which a redox composition is partially applied to the semiconductive functional layer by printing.

13 (New). The method as claimed in claim 4 in which a redox composition is partially applied to the semiconductive functional layer by printing.

14. (New). The method as claimed in claim 6 in which a redox composition is partially applied to the semiconductive functional layer by printing.

15 (New). The method as claimed in claim 4 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.

16 (New). The method as claimed in claim 5 in which a time-stable partial oxidation of

the semiconductive functional layer is carried out by an oxidizing agent.

17 (New). The method as claimed in claim 6 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.

18 (New). The method as claimed in claim 7 in which a time-stable partial oxidation of the semiconductive functional layer is carried out by an oxidizing agent.